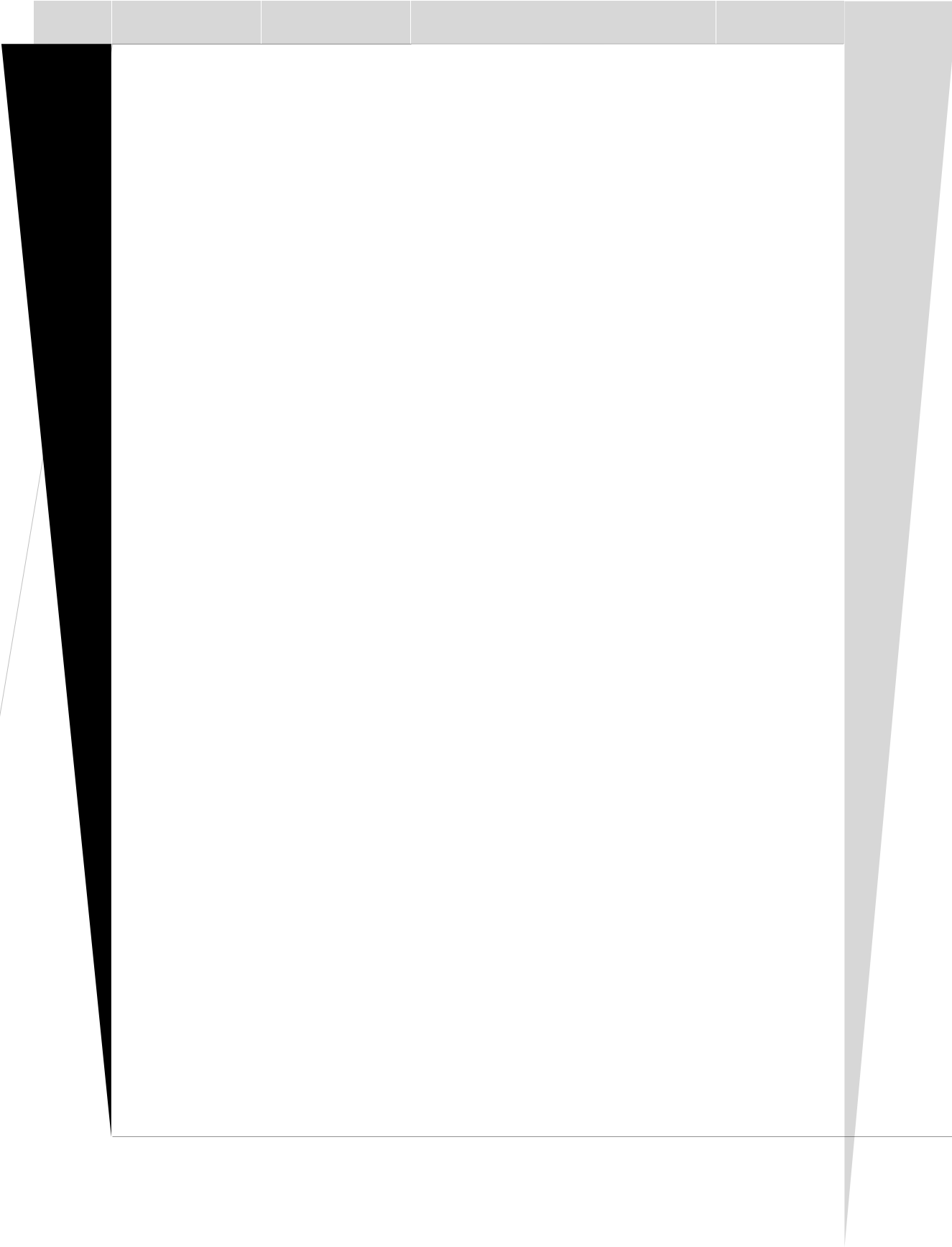
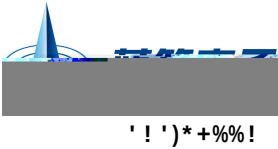
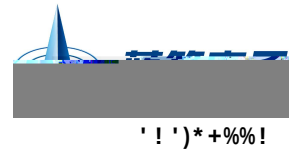






) Silicon NPN Digital transistor in a SOT-23 Plastic Package.

With built-in bias resistors, simplify circuit design, reduce a quantity of parts and manufacturing
proceR

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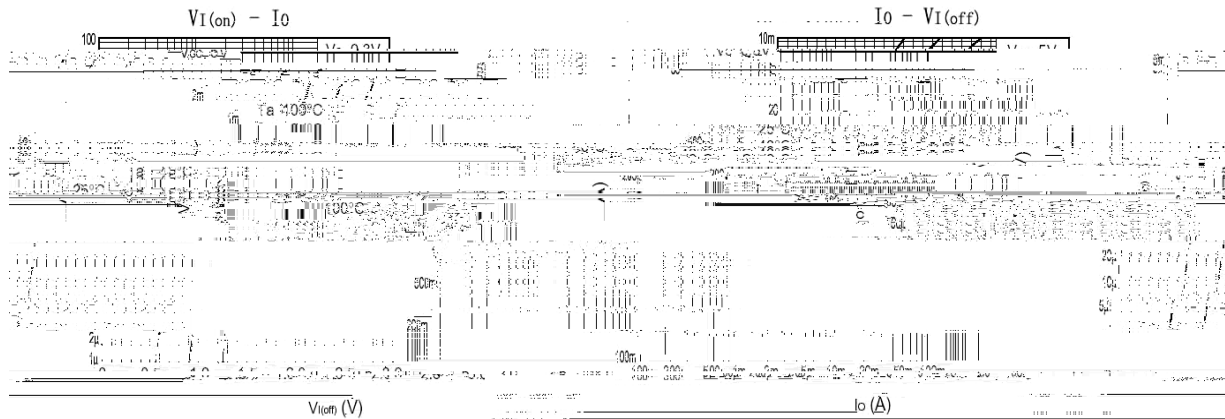
Parameter	Symbol	Rating	Unit
Output Voltage	V_{CC}	50	V
Input Voltage	V_{IN}	40	V
		-10	V
Output Current	I_{CM}	100	mA
	I_O	50	mA
Collector Dissipation	P_C	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 150	°C

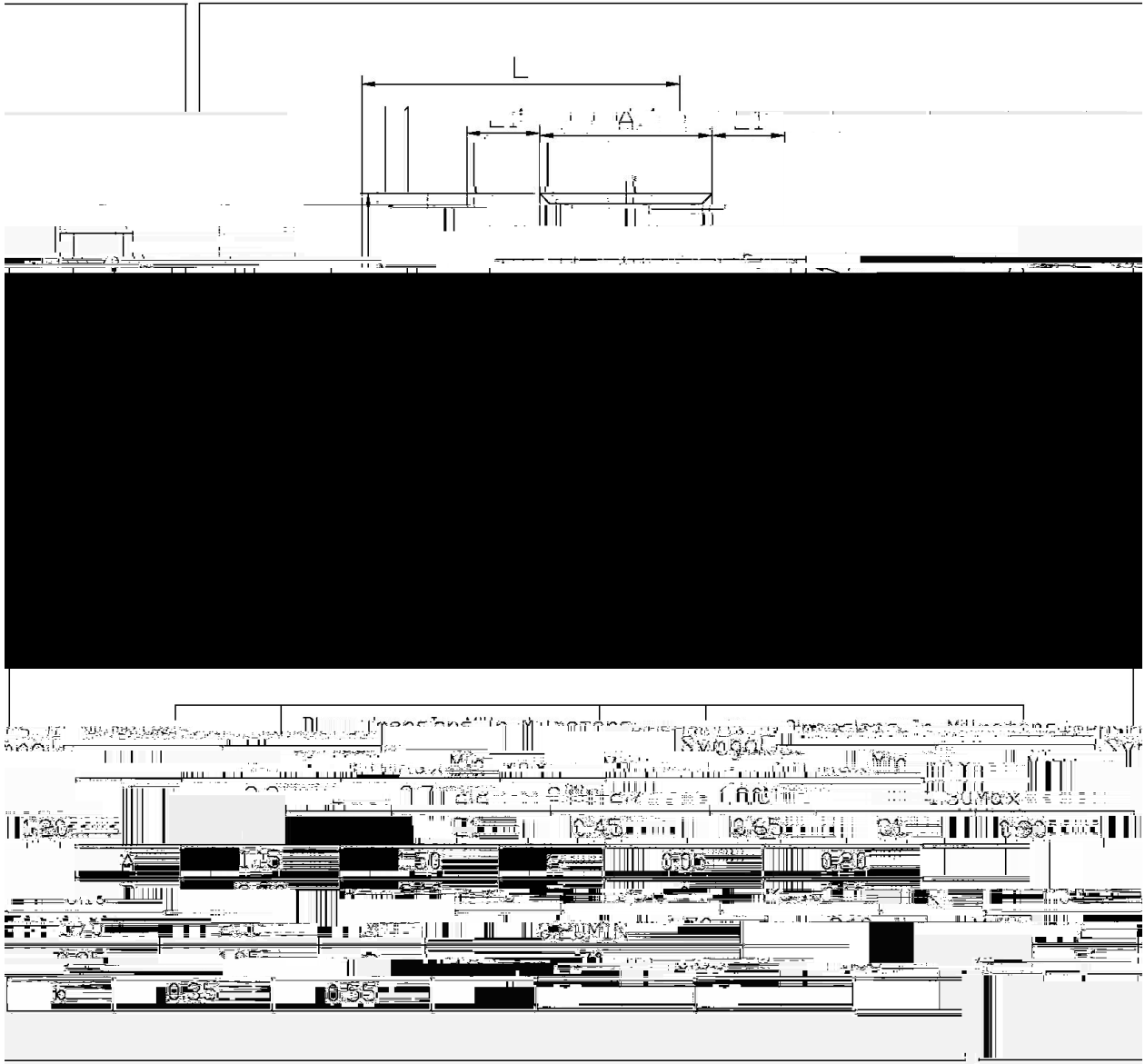
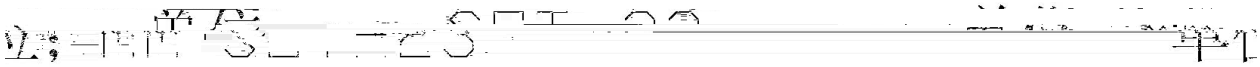
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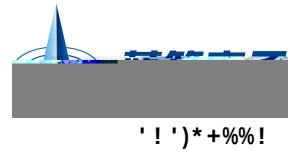
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Voltage	$V_{I(off)}$	$V_{CC}=5.0V$ $I_O=100\mu A$			0.5	V
Input Voltage	$V_{I(on)}$	$V_O=0.3V$ $I_O=10mA$	3			V
Output Voltage	$V_{O(on)}$	$I_O=10mA$ $I_i=0.5mA$			0.3	V
Input Current	I_i	$V_i=5.0V$			0.88	mA
Output Cut-off Current	$I_{O(off)}$	$V_{CC}=50V$ $V_i=0V$			0.5	μA
DC Current Gain	G_I	$V_O=5.0V$ $I_O=5.0mA$	30			
Transition Frequency	f_T	$V_{CE}=10V$ $I_C=5.0mA$ $f=100MHz$		250		MHz
Resistance1	R_1		7	10	13	K Ω
Resistance Ratio	R_2/R_1		0.8	1	1.2	



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